



## 128Kx8 MONOLITHIC FLASH, SMD 5962-96690

### FEATURES

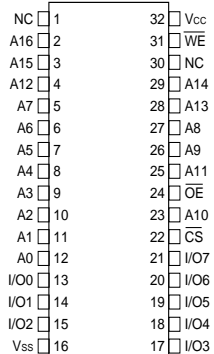
- Access Times of 50\*, 60, 70, 90, 120, 150ns
- Packaging
  - 32 lead, Hermetic Ceramic, 0.400" SOJ (Package 101)
  - 32 pin, Hermetic Ceramic, 0.600" DIP (Package 300)
  - 32 lead, Flatpack (Package 220)
  - 32 lead, Formed Flatpack (Package 221)
  - 32 pin, Rectangular Ceramic Leadless Chip Carrier (Package 601)
- 100,000 Erase/Program Cycles Minimum
- Sector Erase Architecture
  - 8 equal size sectors of 16KBytes each
  - Any combination of sectors can be concurrently erased. Also supports full chip erase
- Organized as 128Kx8
- Commercial, Industrial and Military Temperature Ranges
- 5 Volt Programming. 5V ±10% Supply.
- Low Power CMOS
- Embedded Erase and Program Algorithms
- TTL Compatible Inputs and CMOS Outputs
- Page Program Operation and Internal Program Control Time.

*Note: For programming information refer to Flash Programming 1M5 Application Note.*

*\* The access time of 50ns is available in Industrial and Commercial temperature ranges only.*

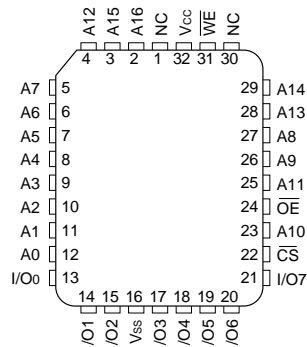
#### PIN CONFIGURATION FOR WMF128K8-XXX5

32 DIP  
32 CSOJ  
32 FLATPACK  
TOP VIEW



#### PIN CONFIGURATION FOR WMF128K8-XCLX5

32 CLCC  
TOP VIEW



#### PIN DESCRIPTION

A0-16	Address Inputs
I/O0-7	Data Input/Output
$\overline{CS}$	Chip Select
$\overline{OE}$	Output Enable
$\overline{WE}$	Write Enable
Vcc	+5.0V Power
Vss	Ground



**ABSOLUTE MAXIMUM RATINGS (1)**

Parameter		Unit
Operating Temperature	-55 to +125	°C
Supply Voltage Range (Vcc)	-2.0 to +7.0	V
Signal voltage range (any pin except A9) (2)	-2.0 to +7.0	V
Storage Temperature Range	-65 to +150	°C
Lead Temperature (soldering, 10 seconds)	+300	°C
Data Retention Mil Temp	10	years
Endurance (write/erase cycles) Mil Temp	10,000 min.	cycles
A9 Voltage for sector protect (V <sub>ID</sub> ) (3)	-2.0 to +14.0	V

**RECOMMENDED OPERATING CONDITIONS**

Parameter	Symbol	Min	Max	Unit
Supply Voltage	V <sub>CC</sub>	4.5	5.5	V
Input High Voltage	V <sub>IH</sub>	2.0	V <sub>CC</sub> + 0.3	V
Input Low Voltage	V <sub>IL</sub>	-0.5	+0.8	V
Operating Temp. (Mil.)	T <sub>A</sub>	-55	+125	°C
Operating Temp. (Ind.)	T <sub>A</sub>	-40	+85	°C
A9 Voltage for Sector Protect	V <sub>ID</sub>	11.5	12.5	V

**CAPACITANCE**  
(T<sub>A</sub> = +25°C)

Parameter	Symbol	Conditions	Max	Unit
Address Input capacitance	C <sub>Ad</sub>	V <sub>I/O</sub> = 0 V, f = 1.0 MHz	15	pF
Output Enable capacitance	C <sub>OE</sub>	V <sub>IN</sub> = 0 V, f = 1.0 MHz	15	pF
Write Enable capacitance	C <sub>WE</sub>	V <sub>IN</sub> = 0 V, f = 1.0 MHz	15	pF
Chip Select capacitance	C <sub>CS</sub>	V <sub>IN</sub> = 0 V, f = 1.0 MHz	15	pF
Data I/O capacitance	C <sub>I/O</sub>	V <sub>I/O</sub> = 0 V, f = 1.0 MHz	15	pF

This parameter is guaranteed by design but not tested.

**NOTES:**

- Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability.
- Minimum DC voltage on input or I/O pins is -0.5V. During voltage transitions, inputs may overshoot V<sub>SS</sub> to -2.0 V for periods of up to 20ns. Maximum DC voltage on output and I/O pins is V<sub>CC</sub> + 0.5V. During voltage transitions, outputs may overshoot to V<sub>CC</sub> + 2.0 V for periods of up to 20ns.
- Minimum DC input voltage on A9 pin is -0.5V. During voltage transitions, A9 may overshoot V<sub>SS</sub> to -2V for periods of up to 20ns. Maximum DC input voltage on A9 is +13.5V which may overshoot to 14.0 V for periods up to 20ns.

**DC CHARACTERISTICS - CMOS COMPATIBLE**  
(V<sub>CC</sub> = 5.0V, V<sub>SS</sub> = 0V, T<sub>A</sub> = -55°C to +125°C)

Parameter	Symbol	Conditions	Min	Max	Unit
Input Leakage Current	I <sub>LI</sub>	V <sub>CC</sub> = 5.5, V <sub>IN</sub> = GND to V <sub>CC</sub>		10	µA
Output Leakage Current	I <sub>LO</sub>	V <sub>CC</sub> = 5.5, V <sub>IN</sub> = GND to V <sub>CC</sub>		10	µA
V <sub>CC</sub> Active Current for Read (1)	I <sub>CC1</sub>	$\overline{CS} = V_{IL}, \overline{OE} = V_{IH}$		35	mA
V <sub>CC</sub> Active Current for Program or Erase (2)	I <sub>CC2</sub>	$\overline{CS} = V_{IL}, \overline{OE} = V_{IH}$		50	mA
V <sub>CC</sub> Standby Current	I <sub>CC3</sub>	V <sub>CC</sub> = 5.5, $\overline{CS} = V_{IH}, f = 5\text{MHz}$		1.6	mA
Output Low Voltage	V <sub>OL</sub>	I <sub>OL</sub> = 8.0 mA, V <sub>CC</sub> = 4.5		0.45	V
Output High Voltage	V <sub>OH1</sub>	I <sub>OH</sub> = -2.5 mA, V <sub>CC</sub> = 4.5	0.85 x V <sub>CC</sub>		V
Output High Voltage	V <sub>OH2</sub>	I <sub>OH</sub> = -100 µA, V <sub>CC</sub> = 4.5	V <sub>CC</sub> - 0.4		V
Low V <sub>CC</sub> Lock Out Voltage	V <sub>LKO</sub>		3.2		V

**NOTES:**

- The I<sub>CC</sub> current listed includes both the DC operating current and the frequency dependent component (at 5 MHz). The frequency component typically is less than 2 mA/MHz, with  $\overline{OE}$  at V<sub>IH</sub>.
- I<sub>CC</sub> active while Embedded Algorithm (program or erase) is in progress.
- DC test conditions: V<sub>IL</sub> = 0.3V, V<sub>IH</sub> = V<sub>CC</sub> - 0.3V

**AC TEST CIRCUIT**

The diagram shows an AC test circuit for a device under test (D.U.T.). It features a bridge circuit with four diodes. A current source is connected to the top node, and another current source is connected to the bottom node. The D.U.T. is connected to the left node. A capacitor C<sub>eff</sub> = 50 pf is connected to the left node. The right node is connected to a bipolar supply V<sub>Z</sub> ≈ 1.5V. Currents I<sub>OL</sub> and I<sub>OH</sub> are indicated at the top and bottom nodes respectively.

**AC TEST CONDITIONS**

Parameter	Typ	Unit
Input Pulse Levels	V <sub>IL</sub> = 0, V <sub>IH</sub> = 3.0	V
Input Rise and Fall	5	ns
Input and Output Reference Level	1.5	V
Output Timing Reference Level	1.5	V

**NOTES:**  
V<sub>Z</sub> is programmable from -2V to +7V.  
I<sub>OL</sub> & I<sub>OH</sub> programmable from 0 to 16mA.  
Tester Impedance Z<sub>0</sub> = 75 Ω.  
V<sub>Z</sub> is typically the midpoint of V<sub>OH</sub> and V<sub>OL</sub>.  
I<sub>OL</sub> & I<sub>OH</sub> are adjusted to simulate a typical resistive load circuit.  
ATE tester includes jig capacitance.



**AC CHARACTERISTICS – WRITE/ERASE/PROGRAM OPERATIONS,  $\overline{WE}$  CONTROLLED**  
 (V<sub>CC</sub> = 5.0V, V<sub>SS</sub> = 0V, T<sub>A</sub> = -55°C to +125°C)

Parameter	Symbol		-50		-60		-70		-90		-120		-150		Unit
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
Write Cycle Time	t <sub>AVAV</sub>	t <sub>WC</sub>	50		60		70		90		120		150		ns
Chip Select Setup Time	t <sub>ELWL</sub>	t <sub>CS</sub>	0		0		0		0		0		0		ns
Write Enable Pulse Width	t <sub>WLWH</sub>	t <sub>WP</sub>	25		30		35		45		50		50		ns
Address Setup Time	t <sub>AVWL</sub>	t <sub>AS</sub>	0		0		0		0		0		0		ns
Data Setup Time	t <sub>DVWH</sub>	t <sub>DS</sub>	25		30		30		45		50		50		ns
Data Hold Time	t <sub>WHDX</sub>	t <sub>DH</sub>	0		0		0		0		0		0		ns
Address Hold Time	t <sub>WLAX</sub>	t <sub>AH</sub>	40		45		45		45		50		50		ns
Chip Select Hold Time	t <sub>WHEH</sub>	t <sub>CH</sub>	0		0		0		0		0		0		ns
Write Enable Pulse Width High	t <sub>WHWL</sub>	t <sub>WPH</sub>	20		20		20		20		20		20		ns
Duration of Byte Programming Operation (min)	t <sub>WHWH1</sub>		14		14		14		14		14		14		μs
Sector Erase Time	t <sub>WHWH2</sub>		2.2	60	2.2	60	2.2	60	2.2	60	2.2	60	2.2	60	sec
Read Recovery Time Before Write	t <sub>GHWL</sub>		0		0		0		0		0		0		ns
V <sub>CC</sub> Setup Time	t <sub>VCS</sub>		50		50		50		50		50		50		μs
Chip Programming Time				12.5		12.5		12.5		12.5		12.5		12.5	sec
Output Enable Setup Time		t <sub>OES</sub>	0		0		0		0		0		0		ns
Output Enable Hold Time (1)		t <sub>OEH</sub>	10		10		10		10		10		10		ns

1. For Toggle and Data Polling.

**AC CHARACTERISTICS – READ ONLY OPERATIONS**  
 (V<sub>CC</sub> = 5.0V, V<sub>SS</sub> = 0V, T<sub>A</sub> = -55°C to +125°C)

Parameter	Symbol		-50		-60		-70		-90		-120		-150		Unit
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max			
Read Cycle Time	t <sub>AVAV</sub>	t <sub>RC</sub>	50		60		70		90		120		150		ns
Address Access Time	t <sub>AVQV</sub>	t <sub>ACC</sub>		50		60		70		90		120		150	ns
Chip Select Access Time	t <sub>ELQV</sub>	t <sub>CE</sub>		50		60		70		90		120		150	ns
$\overline{OE}$ to Output Valid	t <sub>GLQV</sub>	t <sub>OE</sub>		25		30		35		40		50		55	ns
Chip Select to Output High Z (1)	t <sub>EHQZ</sub>	t <sub>DF</sub>		20		20		20		25		30		35	ns
$\overline{OE}$ High to Output High Z (1)	t <sub>GHQZ</sub>	t <sub>DF</sub>		20		20		20		25		30		35	ns
Output Hold from Address, $\overline{CS}$ or $\overline{OE}$ Change, whichever is first	t <sub>AXQX</sub>	t <sub>OH</sub>	0		0		0		0		0		0		ns

1. Guaranteed by design, not tested.

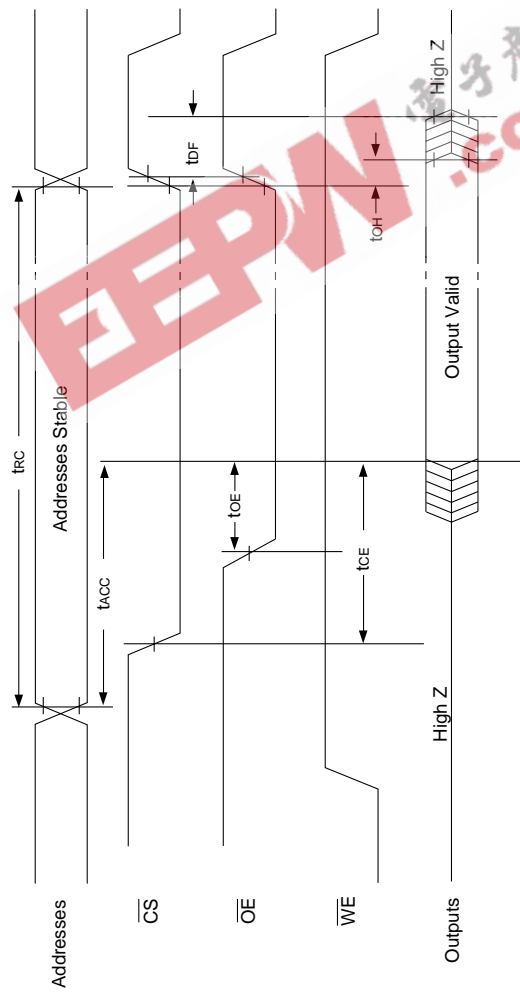


**AC CHARACTERISTICS – WRITE/ERASE/PROGRAM OPERATIONS,  $\overline{CS}$  CONTROLLED**  
 (V<sub>CC</sub> = 5.0V, V<sub>SS</sub> = 0V, T<sub>A</sub> = -55°C to +125°C)

Parameter	Symbol		-50		-60		-70		-90		-120		-150		Unit
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
Write Cycle Time	t <sub>AVAV</sub>	t <sub>WC</sub>	50		60		70		90		120		150		ns
$\overline{WE}$ Setup Time	t <sub>WLLEL</sub>	t <sub>WS</sub>	0		0		0		0		0		0		ns
$\overline{CS}$ Pulse Width	t <sub>ELEH</sub>	t <sub>CP</sub>	25		30		35		45		50		50		ns
Address Setup Time	t <sub>AVEL</sub>	t <sub>AS</sub>	0		0		0		0		0		0		ns
Data Setup Time	t <sub>DVEH</sub>	t <sub>DS</sub>	25		30		30		45		50		50		ns
Data Hold Time	t <sub>EHDX</sub>	t <sub>DH</sub>	0		0		0		0		0		0		ns
Address Hold Time	t <sub>ELAX</sub>	t <sub>AH</sub>	40		45		45		45		50		50		ns
$\overline{WE}$ Hold from $\overline{WE}$ High	t <sub>EHWH</sub>	t <sub>WH</sub>	0		0		0		0		0		0		ns
$\overline{CS}$ Pulse Width High	t <sub>EHEL</sub>	t <sub>CPH</sub>	20		20		20		20		20		20		ns
Duration of Programming Operation	t <sub>WHWH1</sub>		14		14		14		14		14		14		μs
Duration of Erase Operation	t <sub>WHWH2</sub>		2.2	60	2.2	60	2.2	60	2.2	60	2.2	60	2.2	60	sec
Read Recovery before Write	t <sub>GHLEL</sub>		0		0		0		0		0		0		ns
Chip Programming Time				12.5		12.5		12.5		12.5		12.5		12.5	sec

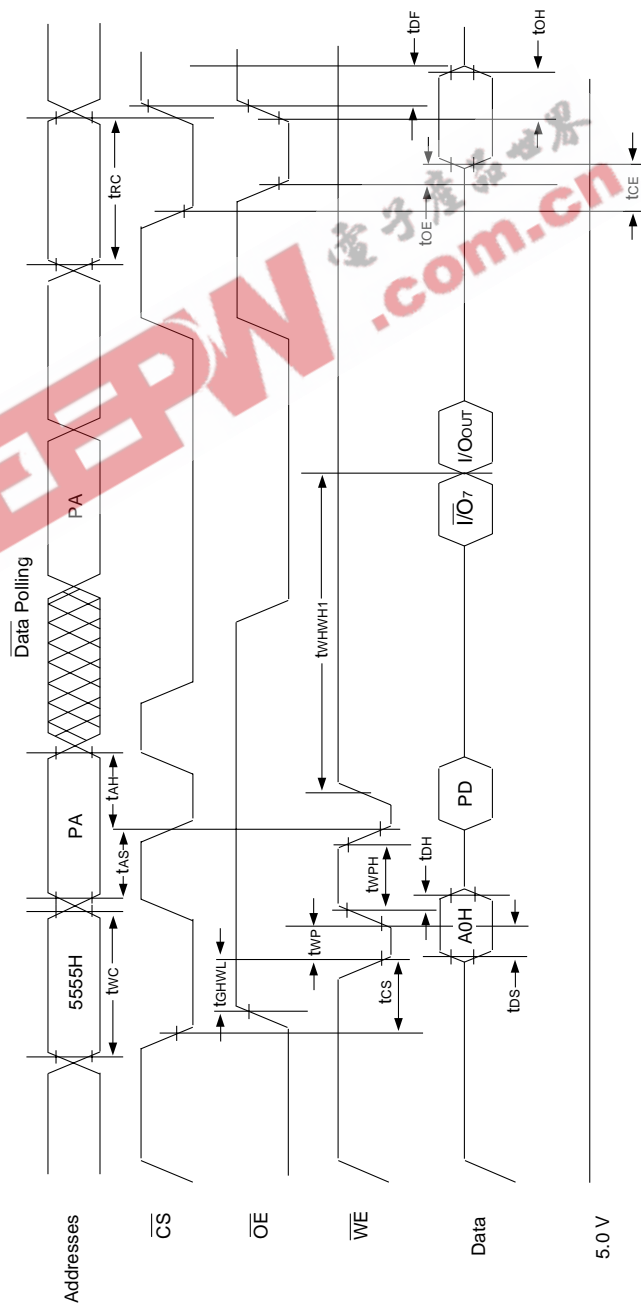


AC WAVEFORMS FOR READ OPERATIONS





WRITE/ERASE/PROGRAM OPERATION, WE CONTROLLED

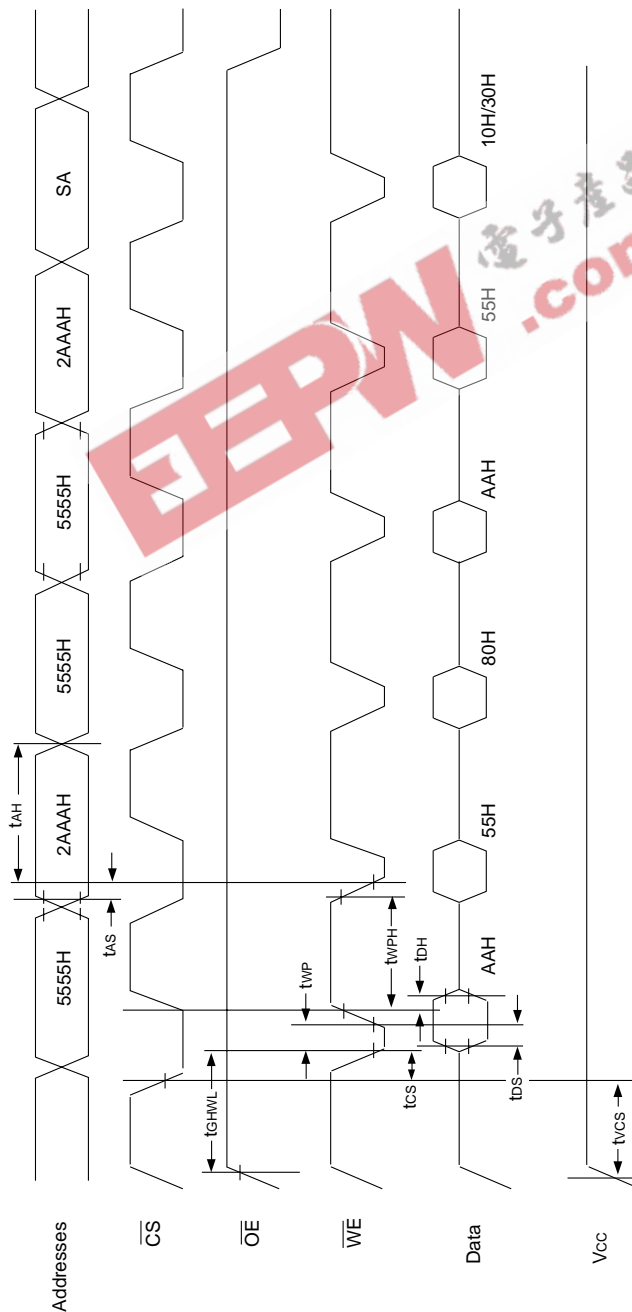


NOTES:

1. PA is the address of the memory location to be programmed.
2. PD is the data to be programmed at byte address.
3. I/O7 is the output of the complement of the data written to the device.
4. I/Oout is the output of the data written to the device.
5. Figure indicates last two bus cycles of four bus cycle sequence.



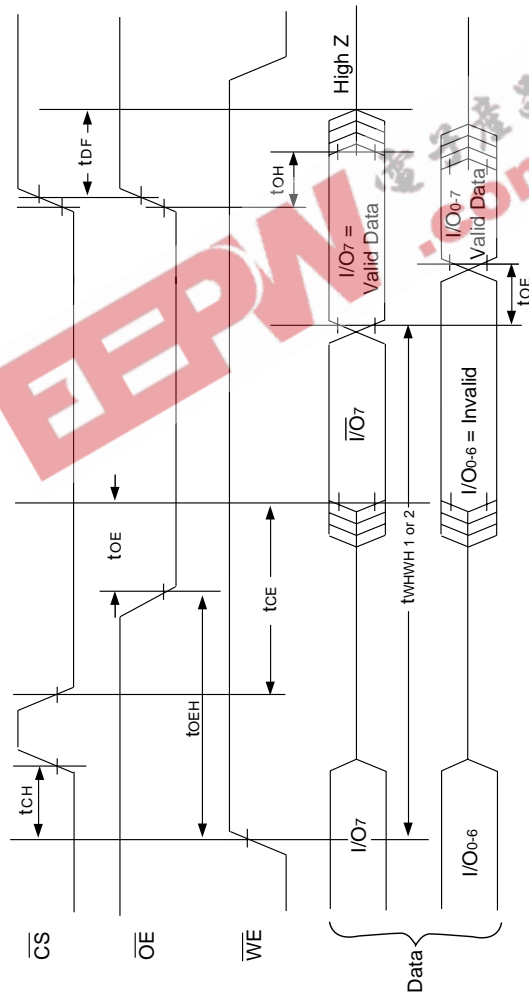
AC WAVEFORMS CHIP/SECTOR ERASE OPERATIONS



**NOTES:**  
1. SA is the sector address for Sector Erase.



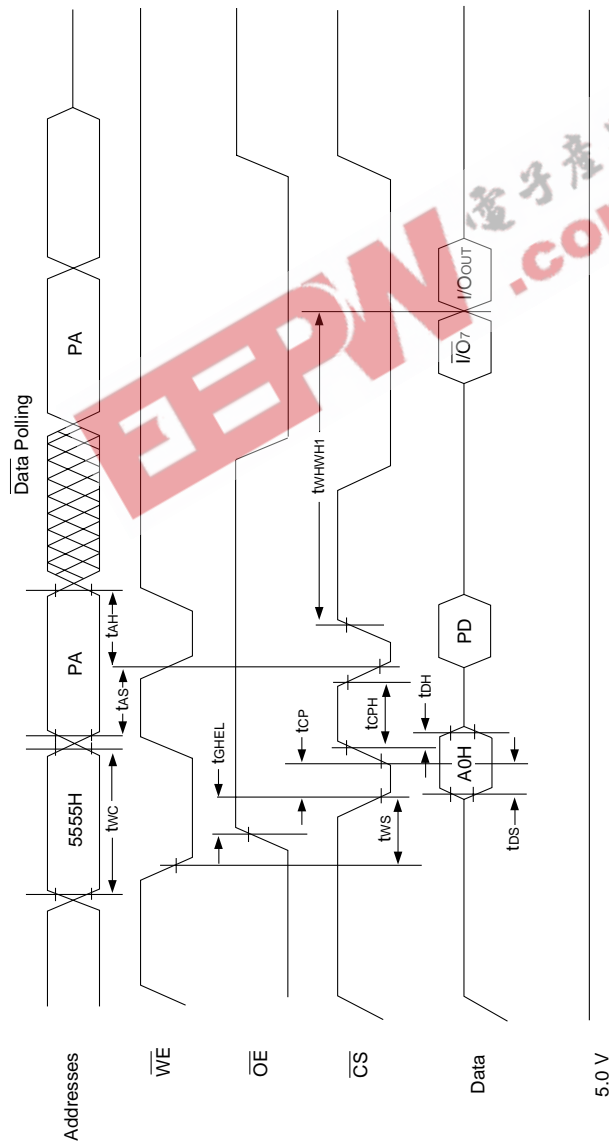
AC WAVEFORMS FOR DATA POLLING DURING EMBEDDED ALGORITHM OPERATIONS







WRITE/ERASE/PROGRAM OPERATION,  $\overline{CS}$  CONTROLLED

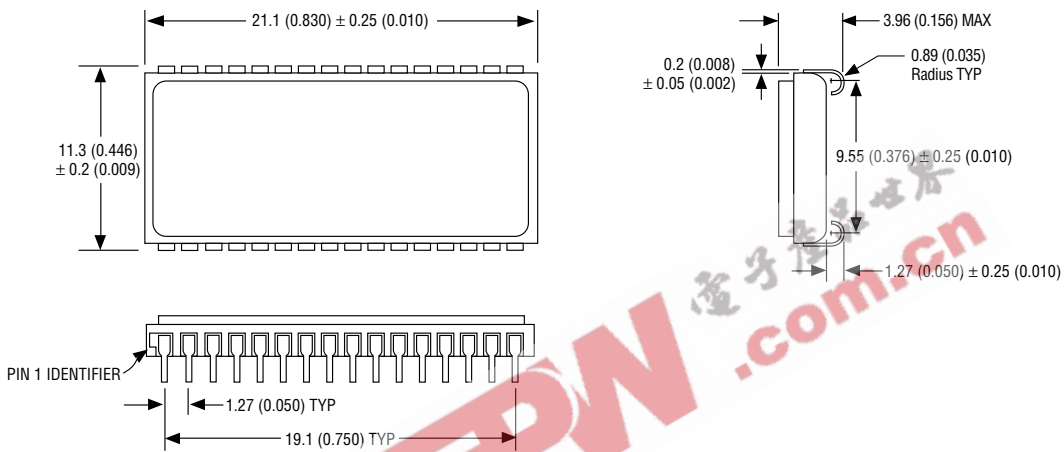


NOTES:

1. PA represents the address of the memory location to be programmed.
2. PD represents the data to be programmed at byte address.
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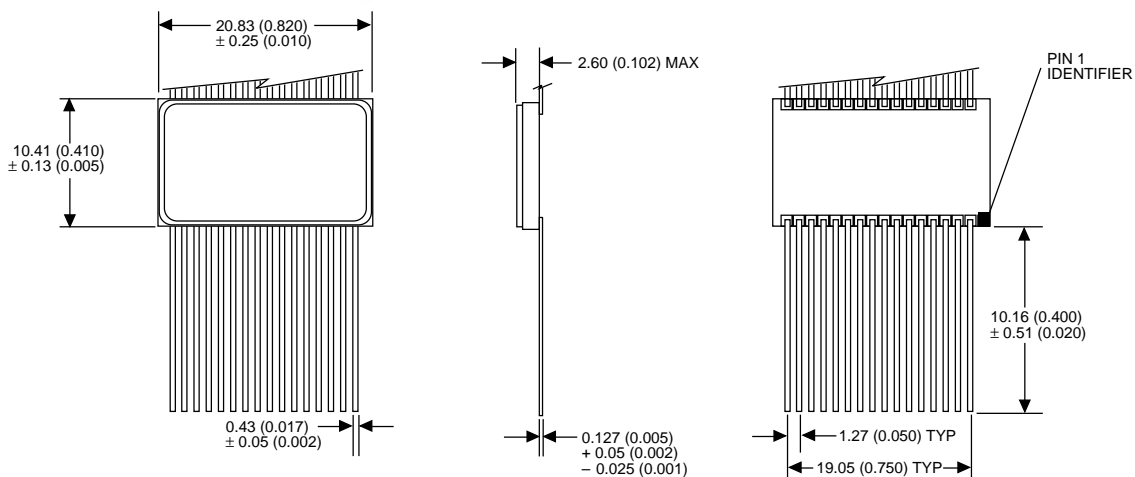


**PACKAGE 101: 32 LEAD, CERAMIC SOJ**



ALL LINEAR DIMENSIONS ARE MILLIMETERS AND PARENTHETICALLY IN INCHES

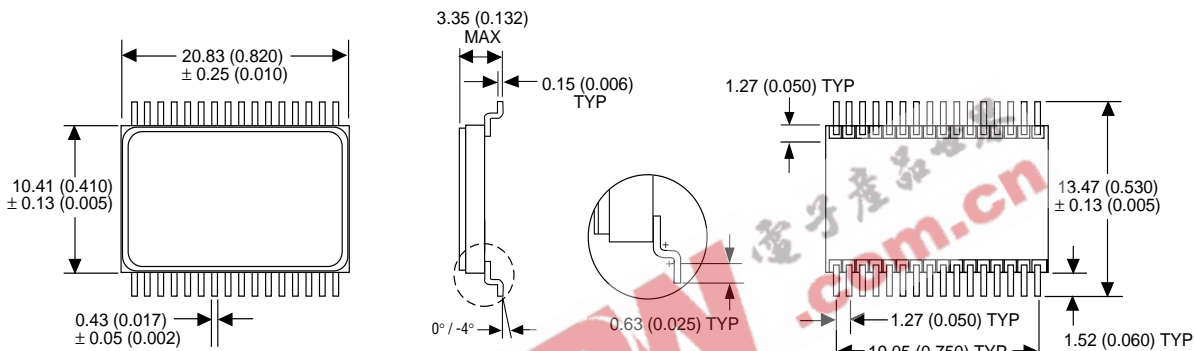
**PACKAGE 220: 32 LEAD, CERAMIC FLATPACK**



ALL LINEAR DIMENSIONS ARE MILLIMETERS AND PARENTHETICALLY IN INCHES

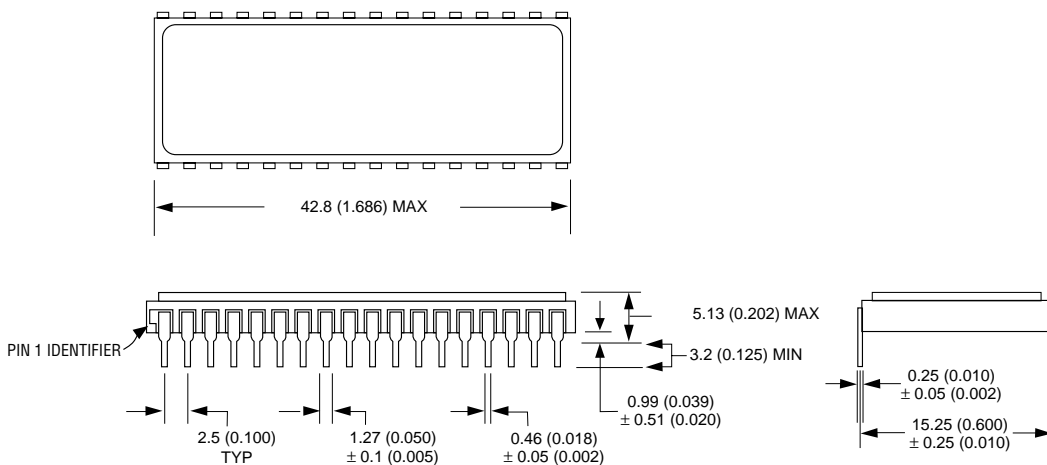


**PACKAGE 221: 32 LEAD, FORMED CERAMIC FLATPACK**



ALL LINEAR DIMENSIONS ARE MILLIMETERS AND PARENTHETICALLY IN INCHES

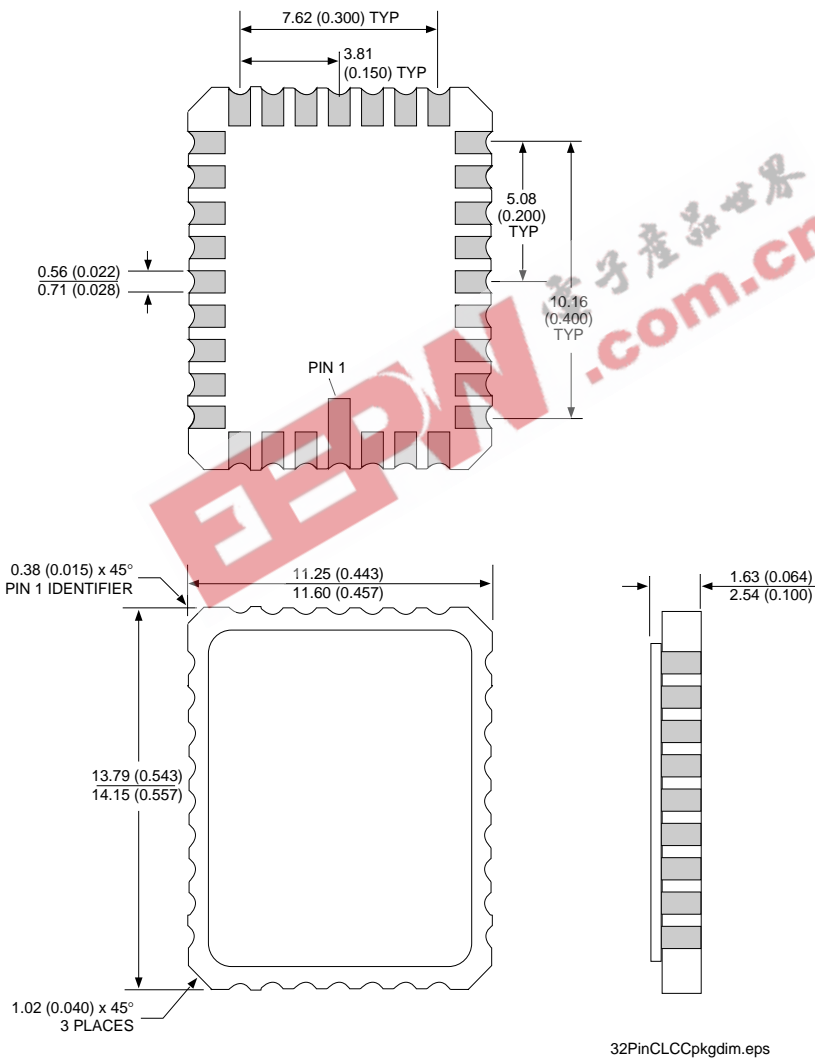
**PACKAGE 300: 32 PIN, CERAMIC DIP, SINGLE CAVITY SIDE BRAZED**



ALL LINEAR DIMENSIONS ARE MILLIMETERS AND PARENTHETICALLY IN INCHES



**PACKAGE 601: 32 PIN, RECTANGULAR CERAMIC LEADLESS CHIP CARRIER**



ALL LINEAR DIMENSIONS ARE MILLIMETERS AND PARENTHETICALLY IN INCHES



ORDERING INFORMATION

W M F 128K8 - XXX X X 5 X

LEAD FINISH:

Blank = Gold plated leads

A = Solder dip leads

V<sub>PP</sub> PROGRAMMING VOLTAGE

5 = 5V

DEVICE GRADE:

Q = MIL-STD-883 Compliant

M = Military Screened -55°C to +125°C

I = Industrial -40°C to +85°C

C = Commercial 0°C to +70°C

PACKAGE TYPE:

DE = 32 Lead Ceramic SOJ (Package 101)

C = 32 Pin Ceramic DIP (Package 300)

FE = 32 Lead Ceramic Flatpack (Package 220)

FF = 32 Lead Formed Ceramic Flatpack (Package 221)

CL = 32 Pin rectangular Ceramic Leadless Chip Carrier (Package 601)

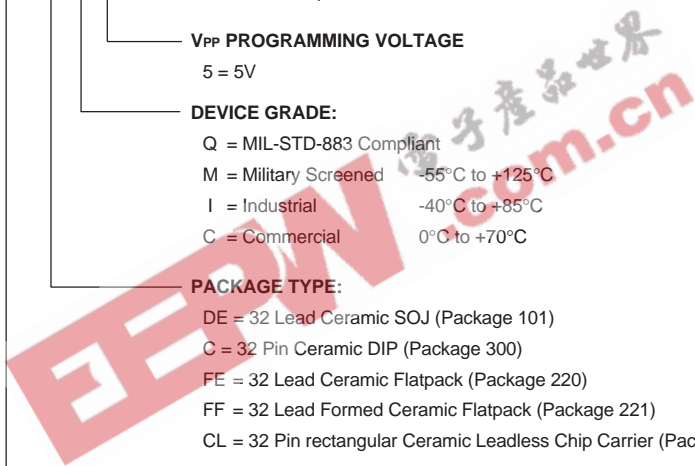
ACCESS TIME (ns)

ORGANIZATION, 128K x 8

Flash

MONOLITHIC

WHITE ELECTRONIC DESIGNS CORP.





DEVICE TYPE	SECTOR SIZE	SPEED	PACKAGE	SMD NO.
128K x 8 Flash Monolithic	16KByte	150ns	32 pin DIP (C)	5962-96690 01HYX
128K x 8 Flash Monolithic	16KByte	120ns	32 pin DIP (C)	5962-96690 02HYX
128K x 8 Flash Monolithic	16KByte	90ns	32 pin DIP (C)	5962-96690 03HYX
128K x 8 Flash Monolithic	16KByte	70ns	32 pin DIP (C)	5962-96690 04HYX
128K x 8 Flash Monolithic	16KByte	60ns	32 pin DIP (C)	5962-96690 05HYX
128K x 8 Flash Monolithic	16KByte	150ns	32 lead SOJ (DE)	5962-96690 01HXX
128K x 8 Flash Monolithic	16KByte	120ns	32 lead SOJ (DE)	5962-96690 02HXX
128K x 8 Flash Monolithic	16KByte	90ns	32 lead SOJ (DE)	5962-96690 03HXX
128K x 8 Flash Monolithic	16KByte	70ns	32 lead SOJ (DE)	5962-96690 04HXX
128K x 8 Flash Monolithic	16KByte	60ns	32 lead SOJ (DE)	5962-96690 05HXX
128K x 8 Flash Monolithic	16KByte	150ns	32 lead Flatpack (FE)	5962-96690 01HTX
128K x 8 Flash Monolithic	16KByte	120ns	32 lead Flatpack (FE)	5962-96690 02HTX
128K x 8 Flash Monolithic	16KByte	90ns	32 lead Flatpack (FE)	5962-96690 03HTX
128K x 8 Flash Monolithic	16KByte	70ns	32 lead Flatpack (FE)	5962-96690 04HTX
128K x 8 Flash Monolithic	16KByte	60ns	32 lead Flatpack (FE)	5962-96690 05HTX
128K x 8 Flash Monolithic	16KByte	150ns	32 lead Formed Flatpack (FF)	5962-96690 01HUX
128K x 8 Flash Monolithic	16KByte	120ns	32 lead Formed Flatpack (FF)	5962-96690 02HUX
128K x 8 Flash Monolithic	16KByte	90ns	32 lead Formed Flatpack (FF)	5962-96690 03HUX
128K x 8 Flash Monolithic	16KByte	70ns	32 lead Formed Flatpack (FF)	5962-96690 04HUX
128K x 8 Flash Monolithic	16KByte	60ns	32 lead Formed Flatpack (FF)	5962-96690 05HUX